General purpose transistor (dual transistors)

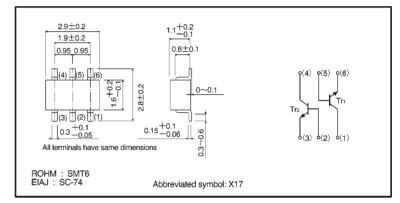
Features

- Two 2SD1484K chips in an SMT package.
- Mounting possible with SMT3 automatic mounting machine.
- Transistor elements are independent, eliminating interference.
- 4) High collector current.Ic = 500mA
- 5) Mounting cost and area can be cut in half.

StructureEpitaxial planar typeNPN silicon transistor

The following characteristics apply to both Tr₁ and Tr₂.

●External dimensions (Units: mm)



■Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol Limits		Unit
Collector-base voltage	Vсво	60	V
Collector-emitter voltage	VCEO	50	V
Emitter-base voltage	VEBO	5	V
Collector current	lc	500	mA
Power dissipation	Pd	300 (TOTAL)	mW *
Junction temperature	Tj	150	င
Storage temperature	Tstg	− 55∼ + 150	Ĉ

*200 mW per element must not be exceeded.

Transistors IMX17

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Collector-base breakdown voltage	ВУсво	60	_	_	٧	Ic=100 μ A	
Collector-emitter breakdown voltage	BVceo	50	_	_	٧	Ic=1mA	
Emitter-base breakdown voltage	ВУЕВО	5	_	_	V	l∈=100 μ A	
Collector cutoff current	Ісво	_	_	0.1	μΑ	Vcb=30V	
Emitter cutoff current	ІЕВО	_	_	0.1	μΑ	V _{EB} =4V	
Collector-emitter saturation voltage	VCE(sat)	_	_	0.6	٧	Ic/Iв=500mA/50mA	
DC current transfer ratio	hfe	120	_	390	_	VcE=3V, Ic=100mA	*
Transition frequency	fτ	_	250	_	MHz	VcE=5V, IE=-20mA, f=100MHz	
Output capacitance	Cob	_	7	_	pF	VcB=10V, IE=0A, f=1MHz	

^{*} Measured using pulse current.

Packaging specifications

	Packaging type	Taping
	Code	T110
Part No.	Basic ordering unit (pieces)	3000
IMX17		0

Electrical characteristic curves

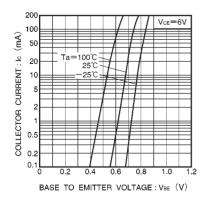


Fig.1 Grounded emitter propagation characteristics

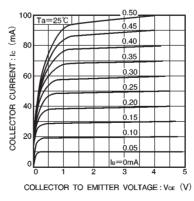


Fig.2 Grounded emitter output characteristics

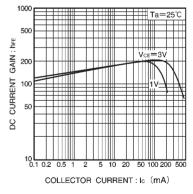


Fig.3 DC current gain vs. collector current (I)

Transistors IMX17

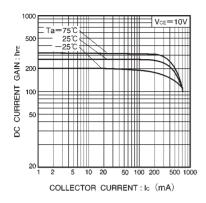


Fig.4 DC current gain vs. collector current (II)

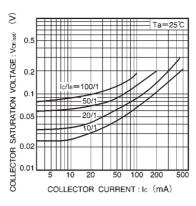


Fig.5 Collector-emitter saturation voltage vs. collector current

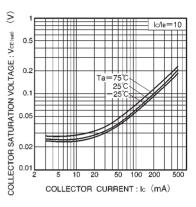


Fig.6 Collector-emitter saturation voltage vs. collector current

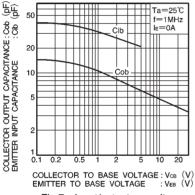


Fig.7 Input/output capacitance vs. voltage

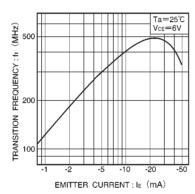


Fig.8 Gain bandwidth product vs. emitter current

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